

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (MACH II  $\pi$ -MOS VI)

## 2SK3936

### Switching Regulator Applications

- Small gate charge:  $Q_g = 60$  nC (typ.)
- Fast reverse recovery time:  $t_{rr} = 380$  ns (typ.)
- Low drain-source ON-resistance:  $R_{DS(ON)} = 0.2$   $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 16.5$  S (typ.)
- Low leakage current:  $I_{DSS} = 500$   $\mu$ A ( $V_{DS} = 500$  V)
- Enhancement mode:  $V_{th} = 2.0$  to  $4.0$  V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

| Characteristic                                       | Symbol         | Rating     | Unit             |
|--|----------------|------------|------------------|
| Drain-source voltage                                 | $V_{DSS}$      | 500        | V                |
| Drain-gate voltage ( $R_{GS} = 20$ k $\Omega$ )      | $V_{DGR}$      | 500        | V                |
| Gate-source voltage                                  | $V_{GSS}$      | $\pm 30$   | V                |
| Drain current  | DC (Note 1)    | $I_D$      | 23               |
|  | Pulse (Note 1) | $I_{DP}$   | 92               |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$          | 150        | W                |
| Single-pulse avalanche energy (Note 2)               | $E_{AS}$       | 759        | mJ               |
| Avalanche current                                    | $I_{AR}$       | 23         | A                |
| Repetitive avalanche energy (Note 3)                 | $E_{AR}$       | 15         | mJ               |
| Channel temperature                                  | $T_{ch}$       | 150        | $^\circ\text{C}$ |
| Storage temperature range                            | $T_{stg}$      | -55 to 150 | $^\circ\text{C}$ |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### Thermal Characteristics

| Characteristic                         | Symbol         | Max   | Unit               |
|--|----------------|-------|--------------------|
| Thermal resistance, channel to case    | $R_{th(ch-c)}$ | 0.833 | $^\circ\text{C/W}$ |
| Thermal resistance, channel to ambient | $R_{th(ch-a)}$ | 50    | $^\circ\text{C/W}$ |

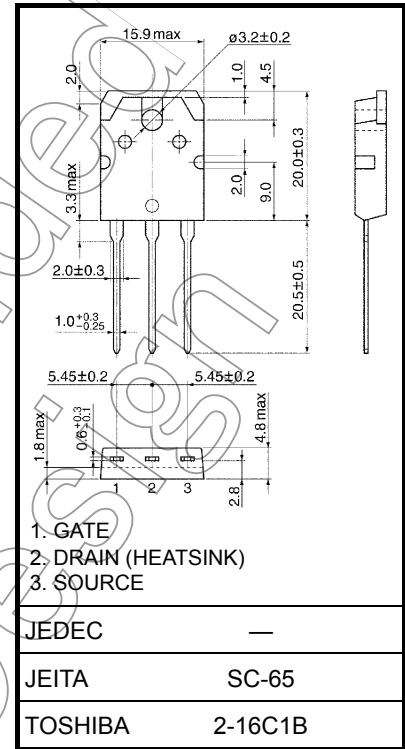
Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2:  $V_{DD} = 90$  V,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 2.44$  mH,  $I_{AR} = 23$  A,  $R_G = 25$   $\Omega$

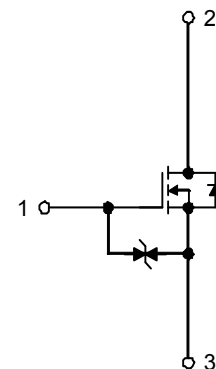
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



Weight: 4.6 g (typ.)



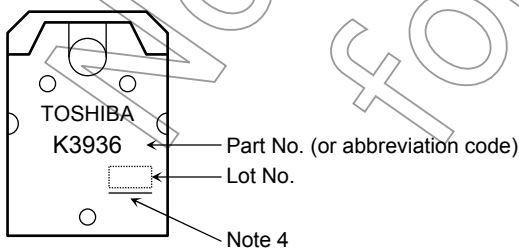
## Electrical Characteristics (Ta = 25°C)

| Characteristic                 |               | Symbol        | Test Condition   | Min                                       | Typ. | Max      | Unit          |
|--------------------------------|---------------|---------------|--|---|------|----------|---------------|
| Gate leakage current           |               | $I_{GSS}$     | $V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$                        | —   | —    | $\pm 10$ | $\mu\text{A}$ |
| Gate-source breakdown voltage  |               | $V_{(BR)GSS}$ | $I_G = \pm 10\ \mu\text{A}, V_{DS} = 0\text{ V}$                       | $\pm 30$                                  | —    | —        | V             |
| Drain cutoff current           |               | $I_{DSS}$     | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$                           | —   | —    | 500      | $\mu\text{A}$ |
| Drain-source breakdown voltage |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$                              | 500                                       | —    | —        | V             |
| Gate threshold voltage         |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$                              | 2.0                                       | —    | 4.0      | V             |
| Drain-source ON-resistance     |               | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 11.5\text{ A}$                            | —   | 0.2  | 0.25     | $\Omega$      |
| Forward transfer admittance    |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 11.5\text{ A}$                            | 8   | 16.5 | —        | S             |
| Input capacitance              |               | $C_{iss}$     | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$          | —   | 4250 | —        | pF            |
| Reverse transfer capacitance   |               | $C_{rss}$     |  | —   | 10   | —        |               |
| Output capacitance             |               | $C_{oss}$     |  | —   | 420  | —        |               |
| Switching time                 | Rise time     | $t_r$         |  | —   | 12   | —        | ns            |
|                                | Turn-on time  | $t_{on}$      |  | —   | 45   | —        |               |
|                                | Fall time     | $t_f$         |  | —   | 10   | —        |               |
|                                | Turn-off time | $t_{off}$     |  | Duty $\leq 1\%$ , $t_w = 10\ \mu\text{s}$ | —    | 80       |               |
| Total gate charge              |               | $Q_g$         | $V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 23\text{ A}$ | —   | 60   | —        | nC            |
| Gate-source charge             |               | $Q_{gs}$      |  | —   | 50   | —        |               |
| Gate-drain charge              |               | $Q_{gd}$      |  | —   | 10   | —        |               |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristic                            | Symbol    | Test Condition                               | Min | Typ. | Max  | Unit          |
|---|-----------|--|-----|------|------|---------------|
| Continuous drain reverse current (Note 1) | $I_{DR}$  | —  | —   | —    | 23   | A             |
| Pulse drain reverse current (Note 1)      | $I_{DRP}$ | —  | —   | —    | 92   | A             |
| Forward voltage (diode)                   | $V_{DSF}$ | $I_{DR} = 23\text{ A}, V_{GS} = 0\text{ V}$  | —   | —    | -1.7 | V             |
| Reverse recovery time                     | $t_{rr}$  | $I_{DR} = 23\text{ A}, V_{GS} = 0\text{ V},$ | —   | 380  | —    | ns            |
| Reverse recovery charge                   | $Q_{rr}$  | $dI_{DR}/dt = 100\text{ A}/\mu\text{s}$      | —   | 2.4  | —    | $\mu\text{C}$ |

### Marking

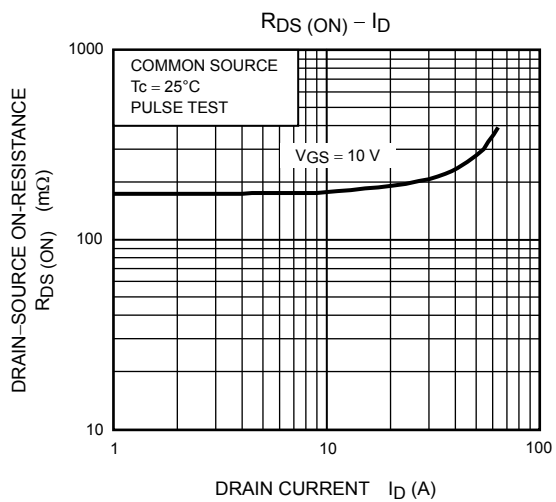
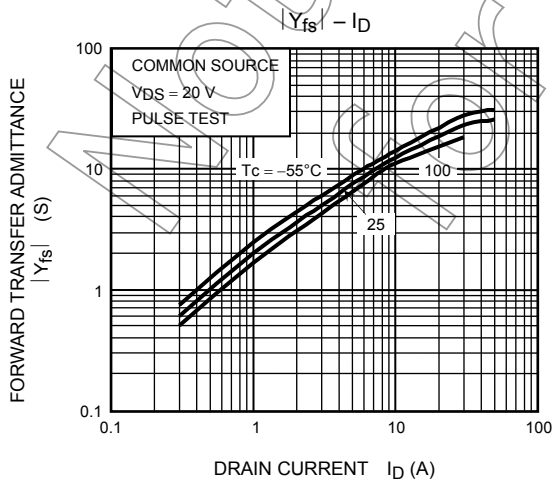
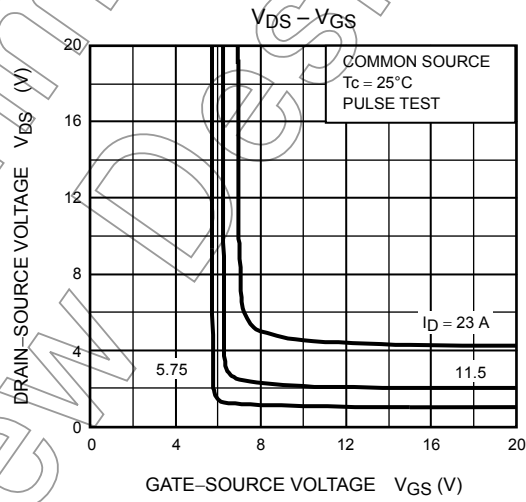
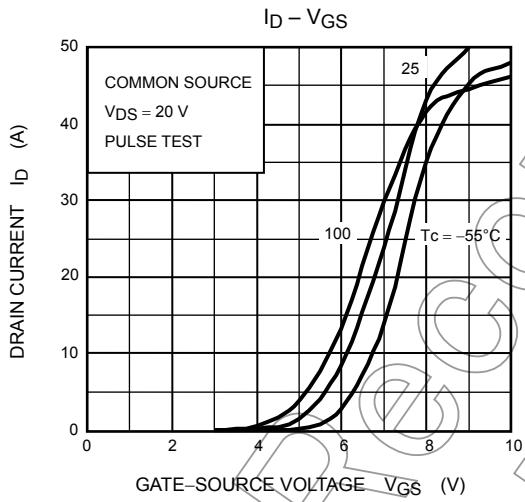
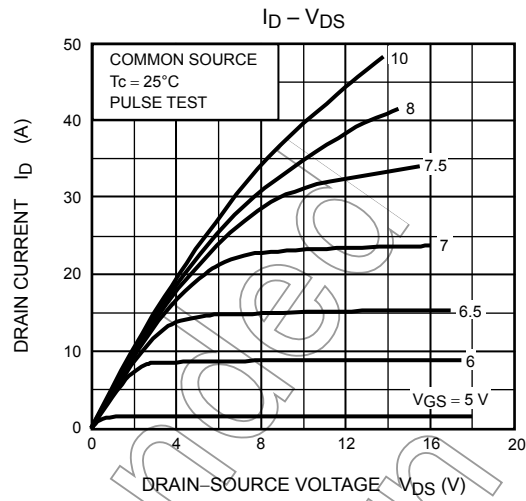
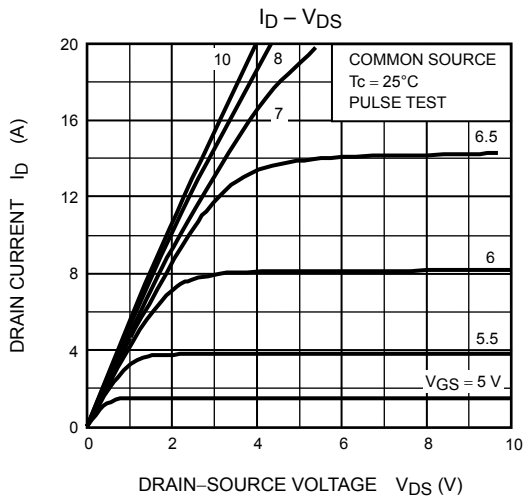


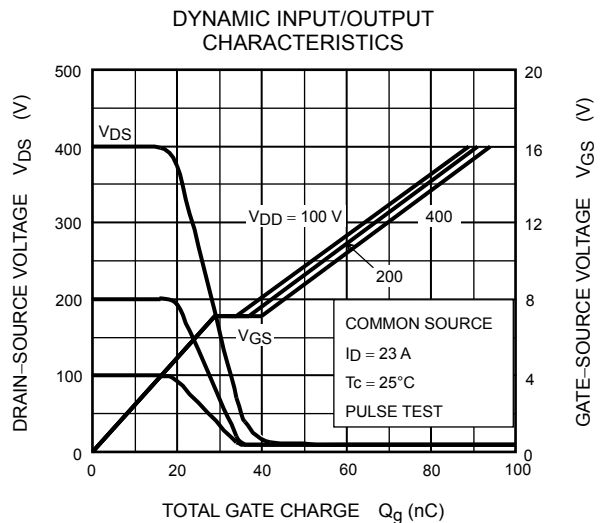
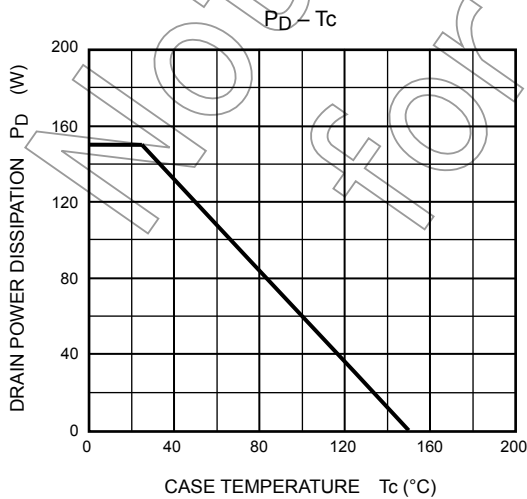
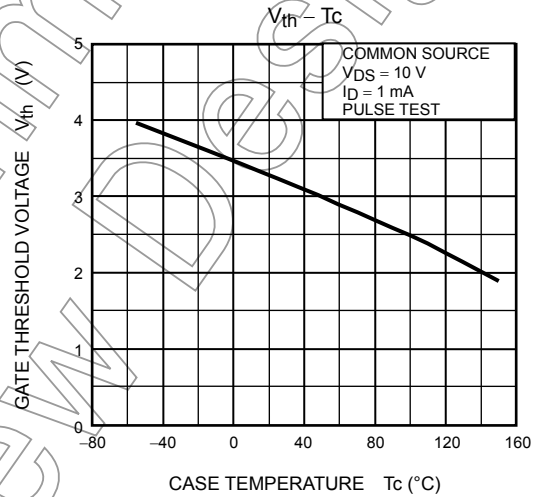
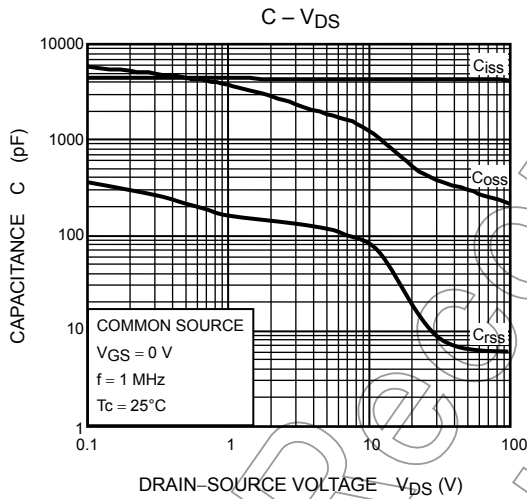
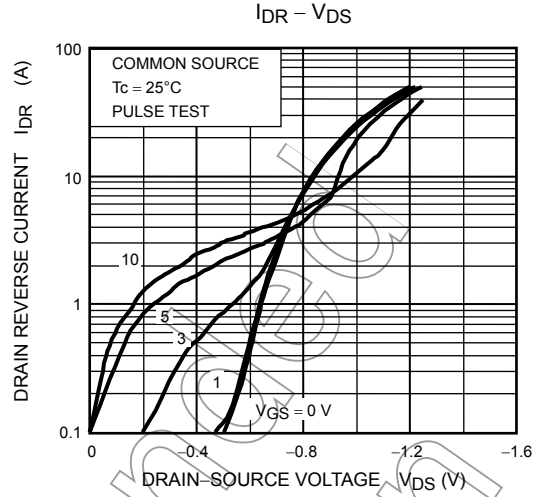
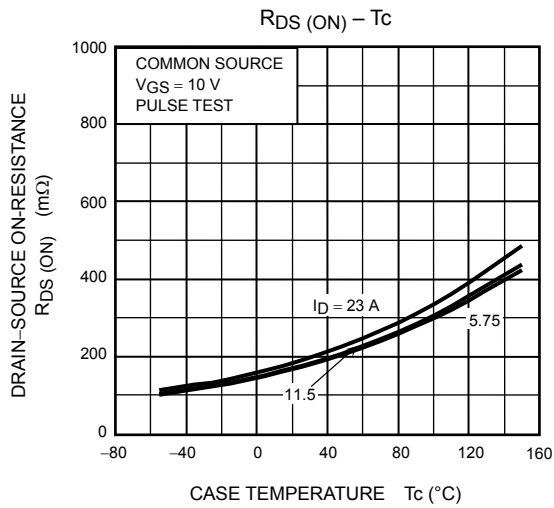
Note 4: A line under a Lot No. identifies the indication of product Labels.

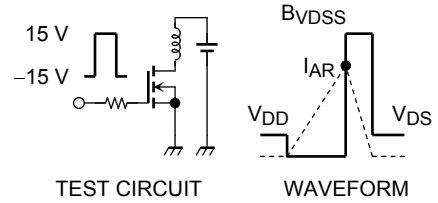
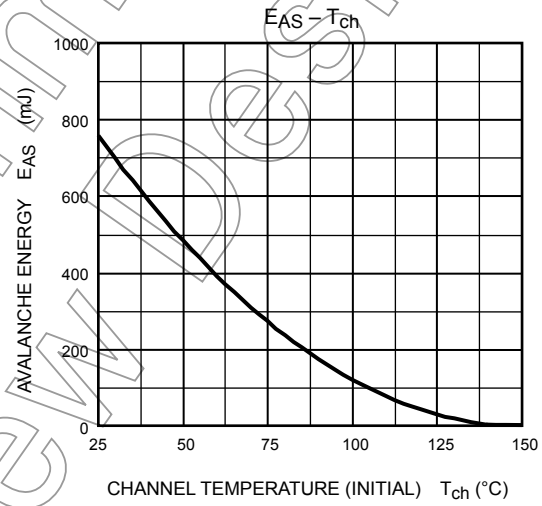
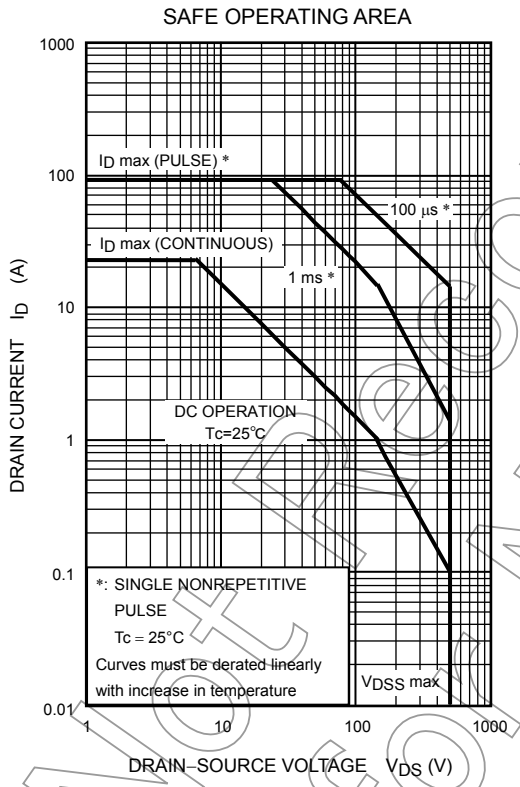
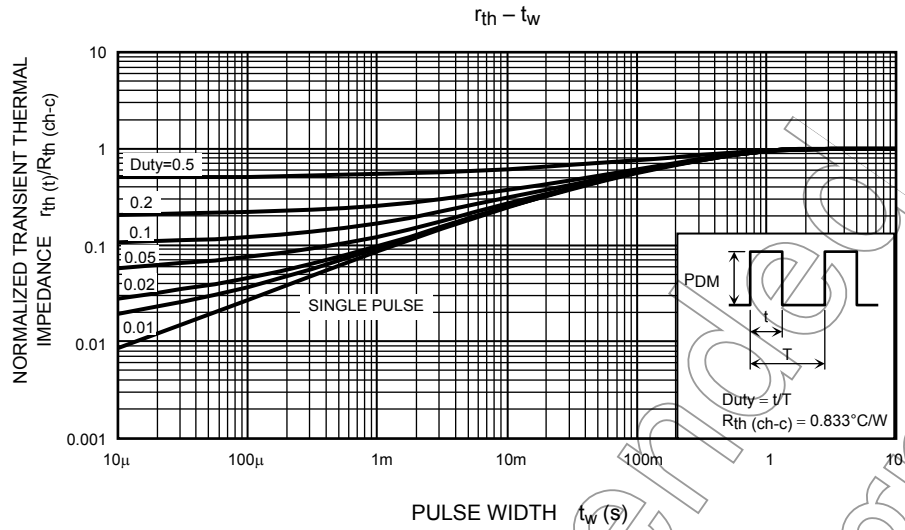
Not underlined:  $[[\text{Pb}]]/\text{INCLUDES} > \text{MCV}$

Underlined:  $[[\text{G}]]/\text{RoHS COMPATIBLE}$  or  $[[\text{G}]]/\text{RoHS} [[\text{Pb}]]$

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$R_G = 25 \Omega$   
 $V_{DD} = 90 V, L = 2.44 mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot i^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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